

Serial No. 09/008,531
Atty. Docket No. MIO 0012 V2

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forming a layer of conductive material over the underlayer and said opening having a topography that includes a substantially vertical component;
forming an overlayer over the said layer of conductive material;
etching a contact hole in said overlayer and in an overetch amount of the substantially vertical component; and
forming a contact in said contact hole disposed adjacent to and directly contacting said vertical component.

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31. (Thrice Amended) A process for making a semiconductor device comprising:
providing a substrate having at least one semiconductor layer;
forming a structure having an opening in said at least one semiconductor layer;
forming a layer of conductive material over said at least one semiconductor layer;
filling said opening with said conductive material to form a substantially vertical component;
forming an overlayer over said layer of conductive material;
forming a contact in said overlayer and in said vertical component disposed adjacent to and contacting said vertical component; and
filling said contact with a conducting material.

Remarks

Claims 21 and 31 have been amended. Claims 26-30, 35, 36, 40-43, and 48 have been canceled. Claims 21-25, and 31-32 are pending in the present application. Claims 21-25 and 31-32 have been rejected.

Election/Restrictions

Upon the Examiner's requirement that a complete reply to the final rejection must include cancellation of nonelected claims or other appropriate action, applicants have canceled claims 26-30, 35-36, 40-43, and 48.